

US-PAT-NO: 5357460

DOCUMENT-IDENTIFIER: US 5357460 A

TITLE: Semiconductor memory device
having two transistors and
at least one ferroelectric
film capacitor

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The gate electrode may use polysilicon, silicide or the like, preferably 500 to 2500.ANG. in thickness, and the bit line and the reversed bit line may use polysilicon, silicide or metals, such as W, Ti, Al-Si or the like, preferably 1000 to 4000.ANG. thick.